Summary
With large-capacity flash memory or when performing low-speed serial programming on a user system, it can take considerable time to rewrite all of the flash memory. This application note describes a method of flash ROM correction in which patches are applied to the user program in a manner that rewrites the smallest area possible.

Unless otherwise specified, the descriptions in this application note apply to the RX113.

Target Device
RX113 Group

When using this application note with other Renesas MCUs, careful evaluation is recommended after making modifications to match the specifications of the alternative MCU.
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1. Specifications

This application note describes a method of updating a user program (referred to below as “ROM correction”) in which a patch program and table data created by the user are written beforehand to the patch area shown in Figure 1.1 and to the table data area shown in Figure 1.2, respectively.

The sample code is executed before the user program runs. When a location corresponding to a patch is reached while the user program is running, the patch program runs, and after execution of the patch program has finished, execution returns to the user program. Figure 1.3 shows an example of the operation of the sample code described in this application note.

Even if writing of the patch program or table data area created by the user fails due to a momentary voltage drop or the like, it is still possible to run the pre-update version of the program. In addition, if writing fails due to a momentary voltage drop or the like while the patch program is being applied, the sample code will retry the process and apply the updated program when the system is restarted.
Figure 1.2 Table Data Area

Before user program runs

User program

User area

User program

Patch program

Location corresponding to patch

Location to be run due to update

User program runs.

Program reaches location corresponding to patch.

Patch program runs.

After patch program runs, return to user program.

Notes:
1. Each patch present/absent determination has three reserved areas with a fixed size of 4 bytes each (total 12 bytes), and the table data is written successively after the reserved areas. The patch present/absent determination has a value of AA55 AA55h.
2. The table data rewrite finished flag is the inverted value of FLG_ADR.

Addresses in red may be changed.

Figure 1.3 Application Note Operation Example
2. Operation Confirmation Conditions

Table 2.1 lists the conditions under which the operation of the sample code referenced in this application note has been confirmed.

Table 2.1  Operation Confirmation Conditions

<table>
<thead>
<tr>
<th>Item</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>MCU used</td>
<td>R5F51138AFP (RX113 Group)</td>
</tr>
<tr>
<td>Operating frequencies</td>
<td>Main clock: 16 MHz&lt;br&gt;Subclock stopped&lt;br&gt;PLL: 32 MHz (main clock: × 1/4 × 8)&lt;br&gt;HOCO stopped&lt;br&gt;System clock (ICLK): 32 MHz (PLL × 1/1)&lt;br&gt;FlashIF clock (FCLK): 32 MHz (PLL × 1/1)</td>
</tr>
<tr>
<td>Operating voltage</td>
<td>3.3 V</td>
</tr>
<tr>
<td>Integrated development environment</td>
<td>Renesas Electronics&lt;br&gt;e2 studio Version 7.7.0</td>
</tr>
<tr>
<td>C compiler</td>
<td>Renesas Electronics&lt;br&gt;C/C++ Compiler Package for RX Family V3.02.00</td>
</tr>
<tr>
<td>Compiler option</td>
<td>Default settings of integrated development environment</td>
</tr>
<tr>
<td>iodefine.h version</td>
<td>Ver. 1.1</td>
</tr>
<tr>
<td>Endian order</td>
<td>Little endian or big endian</td>
</tr>
<tr>
<td>Operating mode</td>
<td>Single-chip mode</td>
</tr>
<tr>
<td>Processor mode</td>
<td>Supervisor mode</td>
</tr>
<tr>
<td>Sample code version</td>
<td>Version 1.00</td>
</tr>
<tr>
<td>Board used</td>
<td>Renesas Starter Kit for RX113 (product number: R0K505113C010BR)</td>
</tr>
</tbody>
</table>
3. **Related Application Notes**

Application notes related to this application note are listed below. Refer to them in conjunction with this application note.

- RX Family Board Support Package Module Using Firmware Integration Technology (R01AN1685)
- RX Family Flash Module Using Firmware Integration Technology (R01AN2184)

Sample code from the above application notes is incorporated into the sample code accompanying this application note. If a newer version is available, use it instead. Visit the Renesas Electronics Corporation website to check for and download the latest version.
4. Software

4.1 Operation Overview

To use ROM correction, create a table data area and patch area to match your specifications. Note that the sample code imposes an upper limit of four on the number of times the patch present/absent determination, patch application area rewrite finished flag, and copy area rewrite finished flag may be written.

Figure 4.1 Table Data Area for ROM Correction

Execute the sample code before running the user program. After the processing corresponding to the patch area and table data area created by the user completes, the user program is run. Figure 4.2 is a flowchart of operation when the sample code is used.

Figure 4.2 Flowchart of Operation Using Sample Code
4.1.1 Table Data Area and Patch Area Checking
When performing ROM correction, the sample code performs the steps shown in Figure 4.3 to check the table data area and patch area.

When performing ROM correction, the sample code performs the steps shown in Figure 4.3 to check the table data area and patch area.

![Figure 4.3 Table Data Area and Patch Area Checking](image)

- **[1]** Check if patch is present/absent.
- **[2]** Check if table data write has finished.
- **[3]** Check target patch area.
- **[4]** Check if rewrite of patch area 0 has finished.
- **[5]** Check target patch application area.
- **[6]** Check if rewrite of patch application area 0 has finished.

Addresses in red may be changed.
4.1.2 ROM Correction Flowchart

Figure 4.4 is a flowchart of ROM correction.

---

**Figure 4.4 ROM Correction Flowchart**

- **ROM correction**
  - **tbl adr = 0, Write upper limit count**
    - Yes: **Write upper limit count** (4)
  - **Read patch present/absent determination**
    - **AA5AAA5Sh?**
      - Yes: **Checks if FLG_ADRy, PP_ADRy, and table data y rewrite finished flag areas are all blank.**
      - No: **y = 0, 1**
    - **tbl adr**
      - Blank? Yes (table data finished)
  - **Rewrite finished?**
    - Yes: **Read FLG_ADRy**
    - No: **Read table data y rewrite finished flag**
      - **Rewrite finished?**
        - Yes: **Read PP_ADRy**
        - No: **Rewrite finished?**
          - Yes: **Write upper limit count** (4)
          - No: **Read patch area y rewrite finished flag**
            - **Rewrite finished?**
              - Yes: **Rewrite with BRK instruction**
              - No: **Blank?**
                - Yes: **Rewrite finished?**
                - No: **z = 0, Write upper limit count - 1, (= 4)**
      - **Read FLG_ADRy**
        - **Blank?**
          - Yes: **Rewrite finished?**
          - No: **y**
            - **Store table data registration count**

---

**Figure 4.4 ROM Correction Flowchart**
4.1.3 Rewrite with BRK Instruction Flowchart
The sample code uses the BRK exception handler, which is called when an address that has been rewritten by ROM correction with the value 00h is executed, as the trigger for running the patch program. Figure 4.5 is a flowchart of the rewrite with BRK instruction processing.

![Rewrite with BRK Instruction Flowchart](image)

**Figure 4.5 Rewrite with BRK Instruction Flowchart**
### 4.1.4 Copy Area Rewrite Procedure

Considering the possibility of write failure due to a momentary voltage drop or the like while the patch application area is being rewritten, the sample code stores to the copy area the contents of the patch application area before it is rewritten. Figure 4.6 shows the copy area rewrite procedure.

1. **[1] Copy patch application area to RAM.**

   ![Figure 4.6](image)

   - **User area**
     - Patch application area (1 block)
   - **Copy area**
   - **RAM area**
     - Patch application area (1 block)

2. **[2] Erase 1 KB block of copy area.**

   ![Figure 4.6](image)

   - **User area**
     - Patch application area (1 block)
   - **Copy area**
     - Block erase
   - **RAM area**
     - Patch application area (1 block)

3. **[3] Copy 1 KB from patch application area from RAM to copy area.**

   ![Figure 4.6](image)

   - **User area**
     - Patch application area (1 block)
   - **Copy area**
     - Patch application area (1 block)
   - **RAM area**
     - Patch application area (1 block)

   **Figure 4.6 Copy Area Rewrite Procedure**
4.1.5 Rewrite with BRK Instruction Procedure

Figure 4.7 shows the rewrite with BRK instruction procedure.

1. Copy patch application area rewrite program to RAM.
2. Change location corresponding to rewrite address in RAM to 00h.
3. Erase 1 KB block of patch application area.
4. Write 1 KB with location rewritten with BRK instruction from RAM to patch application area.

Figure 4.7 Rewrite with BRK Instruction Procedure
4.1.6 Write Procedure for Flags with Allocated Reserved Areas

The processing to write the patch application area rewrite finished flag, copy area rewrite finished flag, and patch present/absent determination, each of which have reserved areas allocated to them, proceeds as follows: If the target area is blank, the item is written to it. If the target area is not blank, a write failure is judged to have occurred due to a momentary voltage drop or the like, the area located at the address 4h ahead of the previous target area becomes the target, and the check to determine if it is blank is repeated.

Figure 4.8 shows the write procedure using the patch application area rewrite finished flag as an example.

[1] If first area for patch application area rewrite finished flag is blank

![Diagram showing write procedure for blank target area]

[2] If first area for patch application area rewrite finished flag is not blank

![Diagram showing write procedure for non-blank target area]

[3] If all areas for patch application area rewrite finished flag are not blank

![Diagram showing write procedure for multiple non-blank target areas]

Patch application area rewrite finished flag cannot be written, so go to error processing.

Figure 4.8 Write Procedure with Patch Application Area Rewrite Finished Flag as Example
4.1.7 Identifying BRK Exception (Unconditional Trap) Occurrence Address

The sample code uses the BRK exception, which occurs when an address that has been rewritten by ROM correction with the value 00h is executed, as the trigger for running the patch program.

When execution of the user program reaches an address to which 00h has been written, that is the rewrite address target location, a BRK exception is generated. The address where the BRK exception occurred is identified by checking the program counter (PC) of the stack area in the BRK exception handler. Figure 4.9 illustrates operation when a BRK exception occurs.

Note: Continues in Figure 4.10.

Figure 4.9 Operation when BRK Exception Occurs
4.1.8 Determination of Patch Processing to Be Run from Address where BRK Exception Occurred

The BRK exception handler compares, via the table data area, the address where the BRK exception occurred with the rewrite addresses in the patch area. It is assumed that addresses are registered in the table data in ascending order, and the comparison proceeds in order, starting from the largest address. Using this method ensures that the latest patch program will be applied even if multiple patches have been applied to the same address. Figure 4.10 illustrates the operation whereby the patch processing to be executed is determined from the address at which the BRK exception occurred.

Note: Even if rewrite address 0 and rewrite address 1 are the same address, the above processing will not apply patch program 0 (the old patch).

Continues in Figure 4.11.

Figure 4.10 Determination of Patch Processing to Be Run from Address where BRK Exception Occurred
4.1.9 Return Setting from BRK Exception Handler

After the patch processing to be executed is determined, the start address of the patch program to be run is set in the program counter (PC) of the stack area in the BRK exception handler, causing execution to return to the patch program after the BRK exception handler. Figure 4.11 illustrates return setting from the BRK exception handler.

Figure 4.11  Return Setting from BRK Exception Handler
4.1.10 Patch Program Execution and Return to User Program

After the BRK exception handler finishes, execution returns to the patch program to be run, and the patch program is executed. After the patch program runs, execution returns to the user program by means of an instruction specified by the user beforehand. Figure 4.12 illustrates the return from the patch program to the user program.

![Figure 4.12 Patch Program Execution](image-url)

- **User program**
  - Area where patch update is complete
  - Table data area (1 block)

- **Patch area**
  - Initial rewrite
  - Rewrite address

- **Patch program**
  - Patch area 0 rewrite finished flag
  - Patch program 0
  - Patch area 1 rewrite finished flag
  - Patch program 1
  - Patch area 2 rewrite finished flag
  - Patch program 2

[10] After return from BRK exception handler, run matching patch program 1.

4.2 Required Memory Sizes
Table 4.1 lists the required memory sizes.

<table>
<thead>
<tr>
<th>Memory Used</th>
<th>Size</th>
<th>Remarks</th>
</tr>
</thead>
<tbody>
<tr>
<td>ROM</td>
<td>1,028 bytes</td>
<td>In r_rom_correct.c module</td>
</tr>
<tr>
<td>RAM</td>
<td>20 bytes</td>
<td>In r_rom_correct.c module</td>
</tr>
<tr>
<td>Patch work area</td>
<td>1,300 bytes</td>
<td>In r_rom_correct.c module</td>
</tr>
<tr>
<td></td>
<td></td>
<td>Size depends on capacity of patch application area to be copied.</td>
</tr>
<tr>
<td></td>
<td></td>
<td>Capacity used in r_flash_rx module</td>
</tr>
</tbody>
</table>

Note: The required memory sizes differ depending on the version of the C compiler and the compile options used. Refer to the applicable application notes for the sizes of r_bsp and r_flash_rx.

4.3 File and Folder Structure
Figure 4.13 shows the source file and folder structure of the sample code. Note that files generated automatically by the integrated development environment are omitted.

```
+ HardwareDebug
  + src
    + snc_gen
      +-- r_bsp
        +-- board
          +-- rskrx113
          +-- user
          +-- doc
            +-- en
            +-- jp
          +-- mcu
            +-- all
            +-- rx113
              +-- register_access
                RX113 register access
        +-- r_config
          +-- r_flash_rx
            +-- doc
            +-- ref
              +-- src
                +-- flash_type_1
                  For flash type 1
                +-- flash_type_2
                  For flash type 2
                +-- flash_type_3
                  For flash type 3
                +-- targets
                  ROM information for each MCU
                +-- rx113
                  Flash definitions for RX113
        +-- r_rom_correct
          +-- rx113
            Flash definitions for RX113
```

The sample code uses the following packages:
- r_bsp (Renesas board support package)
- r_flash_rx (RX Family simple flash module)
4.3.1 src Folder
This folder contains a sample source file and header file used by the ROM correction program.

Table 4.2 Sample Files Used

<table>
<thead>
<tr>
<th>File Name</th>
<th>Description</th>
<th>Notes</th>
</tr>
</thead>
<tbody>
<tr>
<td>main.c</td>
<td>Source file of main routine</td>
<td></td>
</tr>
<tr>
<td>main.h</td>
<td>Header file of main routine</td>
<td></td>
</tr>
</tbody>
</table>

4.3.2 src\_bsp Folder
This folder contains the source files and header files of the Renesas Board Support Package module. For details, refer to the RX Family Board Support Package Module application note.

4.3.3 src\_config Folder
Table 4.3 lists the files in the folder containing the setting files for the target MCU.

Table 4.3 Header Files

<table>
<thead>
<tr>
<th>File Name</th>
<th>Description</th>
<th>Notes</th>
</tr>
</thead>
<tbody>
<tr>
<td>r_bsp_config.h</td>
<td>BSP settings header file</td>
<td>For RSK RX113</td>
</tr>
<tr>
<td>r_flash_rx_config.h</td>
<td>Flash write settings file</td>
<td></td>
</tr>
</tbody>
</table>

4.3.4 src\_flash_rx Folder
This folder contains the source files and header files of the flash FIT module. For details, refer to the Flash Module Firmware Integration Technology application note.

4.3.5 src\_rom_correct Folder
This folder contains the source file and header file of the ROM correction program.

Table 4.4 ROM Correction

<table>
<thead>
<tr>
<th>File Name</th>
<th>Description</th>
<th>Notes</th>
</tr>
</thead>
<tbody>
<tr>
<td>r_rom_correct.c</td>
<td>ROM correction source file</td>
<td></td>
</tr>
<tr>
<td>r_rom_correct.h</td>
<td>ROM correction header file</td>
<td></td>
</tr>
</tbody>
</table>
## 4.4 Option-Setting Memory

Table 4.5 lists the option-setting memory settings used in the sample code. Modify the setting values as necessary to match your system.

### Table 4.5 Option-Setting Memory Settings in Sample Code

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Address</th>
<th>Setting Value</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>OFS0</td>
<td>FFFF FF8Fh to FFFF FF8Ch</td>
<td>FFFF FFFFh</td>
<td>• IWDT stopped after a reset</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>• Timeout duration: 2,048 cycles</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>• IWDT clock division ratio: 1/128</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>• Window start position/end position:</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>Not specified</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>• Resets enabled</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>• Count stop in sleep mode enabled</td>
</tr>
<tr>
<td>OFS1</td>
<td>FFFF FF88h to FFFF FF8Bh</td>
<td>FFFF FFFFh</td>
<td>• Voltage monitor reset disabled at startup</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>• HOCO oscillation disabled after a reset</td>
</tr>
<tr>
<td>MDE</td>
<td>FFFF FF80h to FFFF FF83h</td>
<td>FFFF FFFFh</td>
<td>Little endian</td>
</tr>
</tbody>
</table>
### 4.5 Constants

Table 4.6 lists the constants used in the sample code.

<table>
<thead>
<tr>
<th>Constant Name</th>
<th>Setting Value</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>APPLY_PATCH</td>
<td>AA55 AA55h</td>
<td>Data indicating patch present in patch present/absent determination</td>
</tr>
<tr>
<td>PATCH_TARGET_REWRITE</td>
<td>7061 6368h</td>
<td>Data indicating rewrite finished in patch application area rewrite finished flag</td>
</tr>
<tr>
<td>COPY_AREA_REWRITE</td>
<td>636F 7079h</td>
<td>Data indicating rewrite finished in copy area rewrite finished flag</td>
</tr>
<tr>
<td>LMT_WRITE_TIMES</td>
<td>4</td>
<td>Write count upper limit value of patch application area rewrite finished flag, copy area rewrite finished flag, and patch present/absent determination</td>
</tr>
<tr>
<td>REWRITE_FLG_AREA_SIZE</td>
<td>LMT_WRITE_TIMES * 4</td>
<td>Area size of patch application area rewrite finished flag, copy area rewrite finished flag, and patch present/absent determination</td>
</tr>
<tr>
<td>BRK_CODE</td>
<td>00h</td>
<td>Code indicating BRK instruction</td>
</tr>
<tr>
<td>FLASH_RETRY_TIMES</td>
<td>3</td>
<td>Retry count when flash-related error occurs*1</td>
</tr>
<tr>
<td>FLASH_BLOCK_TOP_MASK</td>
<td>FFFF FC00h</td>
<td>Mask for acquiring start address of flash block</td>
</tr>
<tr>
<td>TABLE_DATA_AREA_TOP_ADR</td>
<td>FFFF C000h</td>
<td>Start address of table data area</td>
</tr>
<tr>
<td>APPLY_PATCH_ADR</td>
<td>TABLE_DATA_AREA_TOP_ADR</td>
<td>Start address of patch present/absent determination</td>
</tr>
<tr>
<td>TABLE_DATA_TOP_ADR</td>
<td>TABLE_DATA_AREA_TOP_ADR+REWRITE_FLG_AREA_SIZE</td>
<td>Table data start address (excluding patch present/absent determination)</td>
</tr>
<tr>
<td>PATCH_AREA_TOP_ADR</td>
<td>TABLE_DATA_AREA_TOP_ADR+FLASH_CF_BLOCK_SIZE</td>
<td>Start address of patch area</td>
</tr>
<tr>
<td>COPY_AREA_TOP_ADR</td>
<td>FFFF F000h</td>
<td>Start address of copy area</td>
</tr>
<tr>
<td>TABLE_DATA_NUM_MAX</td>
<td>(COPY_AREA_TOP_ADR-TABLE_DATA_TOP_ADR) / (sizeof(table_data_t))</td>
<td>Maximum table data count</td>
</tr>
</tbody>
</table>

Note: 1. In the sample code, when a flash-related error occurs, an error is reported when the error continues up to the retry count specified by this setting.
4.6 Structure Listing

Figure 4.14 lists the structures used in the sample code.

typedef struct
{
    uint32_t flg_adr;        /* FLG_ADR */
    uint32_t pp_adr;         /* PP_ADR */
    uint32_t table_rewrite_flg;  /* Table data rewrite finished flag */
} table_data_t;

typedef struct
{
    uint32_t patch_rewrite_flg;  /* Patch area rewrite finished flag */
    uint32_t rewrite_adr;       /* Rewrite address */
    uint8_t * ppatch_prg;       /* Pointer to start address of patch program */
} patch_data_t;

Figure 4.14 Structures Used in Sample Code

4.7 Enumeration Listing

Figure 4.15 lists the enumerated types used in the sample code. Also included is flash_err_t, a structure for the RX Family simple flash module used by the sample code, so refer to it as well.

typedef enum
{
    ROM_CORRECT_SUCCESS = 0,
    ROM_CORRECT_ERR_BUSY,
    ROM_CORRECT_ERR_ACCESSW,
    ROM_CORRECT_ERR_FAILURE,
    ROM_CORRECT_ERR_CMD_LOCKED,
    ROM_CORRECT_ERR_LOCKBIT_SET,
    ROM_CORRECT_FREQUENCY,
    ROM_CORRECT_ALIGNED,
    ROM_CORRECT_BOUNDARY,
    ROM_CORRECT_OVERFLOW,
    ROM_CORRECT_ERR_BYTES,
    ROM_CORRECT_ERR_ADDRESS,
    ROM_CORRECT_ERR_BLOCKS,
    ROM_CORRECT_ERR_PARAM,
    ROM_CORRECT_ERR_NULL_PTR,
    ROM_CORRECT_TIMEOUT,
    ROM_CORRECT_ERR_TABLE,     /* Table data area error */
    ROM_CORRECT_ERR_PATCH,     /* Patch area error */
    ROM_CORRECT_ERR_COPY_AREA_FLG, /* Copy area rewrite finished flag write error */
    ROM_CORRECT_ERR_PATCH_AREA_FLG, /* Patch application area rewrite finished flag write error */
    ROM_CORRECT_NOT_APPLY      /* No valid data in patch present/absent determination */
} rom_correct_err_t;

Figure 4.15 Enumerated Types Used in Sample Code
4.8 Variables
Table 4.7 lists the variables used in the sample code.

<table>
<thead>
<tr>
<th>Type</th>
<th>Variable Name</th>
<th>Description</th>
<th>Used by Function</th>
</tr>
</thead>
<tbody>
<tr>
<td>static uint8_t</td>
<td>table_data_num</td>
<td>Table data registration count</td>
<td>• R_ROM_Correct</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>• setting_patch</td>
</tr>
</tbody>
</table>

4.9 Functions
Table 4.8 lists the functions used in the sample code.

<table>
<thead>
<tr>
<th>Function Name</th>
<th>Description</th>
</tr>
</thead>
<tbody>
<tr>
<td>R_ROM_Correct</td>
<td>ROM correction processing</td>
</tr>
<tr>
<td>R_ROM_MakePatch</td>
<td>Go to applicable patch program (BRK exception handler)</td>
</tr>
<tr>
<td>get_brk_address</td>
<td>Get BRK exception occurrence address</td>
</tr>
<tr>
<td>set_return_adr</td>
<td>Set return address to corresponding patch program</td>
</tr>
<tr>
<td>chk_apply_patch</td>
<td>Patch present/absent determination processing</td>
</tr>
<tr>
<td>setting_patch</td>
<td>Set patch to register</td>
</tr>
<tr>
<td>chk_patch</td>
<td>Check patch to register</td>
</tr>
<tr>
<td>chk_table_data</td>
<td>Check table data</td>
</tr>
<tr>
<td>chk_patch_area</td>
<td>Check patch area</td>
</tr>
<tr>
<td>chk_rewrite_patch_target_area</td>
<td>Check patch application area rewrite</td>
</tr>
<tr>
<td>rewrite_patch_target_area</td>
<td>Patch application area rewrite processing</td>
</tr>
<tr>
<td>chk_rewrite_copy_area</td>
<td>Check copy area rewrite</td>
</tr>
<tr>
<td>rewrite_copy_area</td>
<td>Copy area rewrite processing</td>
</tr>
<tr>
<td>rewrite_brk_code</td>
<td>Rewrite patch application area with BRK instruction</td>
</tr>
<tr>
<td>call_R_FLASH_Open</td>
<td>Flash FIT module initialization, including retry in case of error</td>
</tr>
<tr>
<td>call_R_FLASH_Erase</td>
<td>Erase flash, including retry in case of error</td>
</tr>
<tr>
<td>call_R_FLASH_BlankCheck</td>
<td>Flash blank check, including retry in case of error</td>
</tr>
<tr>
<td>call_R_FLASH_Write</td>
<td>Write to flash, including retry in case of error</td>
</tr>
</tbody>
</table>
4.10 Function Specifications

The following tables list the sample code function specifications.

**R_ROM_Correct**

<table>
<thead>
<tr>
<th>Outline</th>
<th>ROM correction function</th>
</tr>
</thead>
<tbody>
<tr>
<td>Header</td>
<td>r_rom_correct.h</td>
</tr>
<tr>
<td>Declaration</td>
<td>rom_correct_err_t R_ROM_Correct (void)</td>
</tr>
<tr>
<td>Description</td>
<td>ROM correction processing</td>
</tr>
<tr>
<td>Arguments</td>
<td>None</td>
</tr>
<tr>
<td>Return Value</td>
<td>ROM correction setting result</td>
</tr>
<tr>
<td></td>
<td>ROM_CORRECT_SUCCESS: Success</td>
</tr>
<tr>
<td></td>
<td>ROM_CORRECT_ERR_BUSY: Software command running, or flash FIT module not initialized</td>
</tr>
<tr>
<td></td>
<td>ROM_CORRECT_ERR_FAILURE: Flash blank check, erase, or write failure</td>
</tr>
<tr>
<td></td>
<td>ROM_CORRECT_ERR_BYTES: Flash write or blank check size error</td>
</tr>
<tr>
<td></td>
<td>ROM_CORRECT_ERR_ADDRESS: Invalid address setting</td>
</tr>
<tr>
<td></td>
<td>ROM_CORRECT_ERR_BLOCKS: Invalid flash block number</td>
</tr>
<tr>
<td></td>
<td>ROM_CORRECT_ERR_TABLE: Table data area setting error</td>
</tr>
<tr>
<td></td>
<td>ROM_CORRECT_ERR_PATCH: Patch area setting error</td>
</tr>
<tr>
<td></td>
<td>ROM_CORRECT_ERR_WR_COPY_FLAG: Copy area rewrite finished flag write error</td>
</tr>
<tr>
<td></td>
<td>ROM_CORRECT_ERR_WR_PATCH_FLAG: Patch application area rewrite finished flag write error</td>
</tr>
<tr>
<td>Remarks</td>
<td>Except for ROM_CORRECT_NOT_APPLY, the last registered table data setting result is sent as the return value.</td>
</tr>
<tr>
<td></td>
<td>If setting result information is needed for each table data item, register each table data item and patch area individually.</td>
</tr>
</tbody>
</table>

**R_ROM_MakePatch**

<table>
<thead>
<tr>
<th>Outline</th>
<th>Go to applicable patch program (BRK exception handler)</th>
</tr>
</thead>
<tbody>
<tr>
<td>Header</td>
<td>r_rom_correction.h</td>
</tr>
<tr>
<td>Declaration</td>
<td>void R_ROM_MakePatch (void)</td>
</tr>
<tr>
<td>Description</td>
<td>Determines the applicable patch program from the address at which the BRK exception occurred and transitions to it.</td>
</tr>
<tr>
<td>Arguments</td>
<td>None</td>
</tr>
<tr>
<td>Return Value</td>
<td>None</td>
</tr>
<tr>
<td>Remarks</td>
<td>This function is a BRK exception handler.</td>
</tr>
</tbody>
</table>
### get_brk_address

<table>
<thead>
<tr>
<th>Outline</th>
<th>Get BRK exception occurrence address</th>
</tr>
</thead>
<tbody>
<tr>
<td>Header</td>
<td>r_rom_correction.h</td>
</tr>
<tr>
<td>Declaration</td>
<td>uint32_t get_brk_address (void)</td>
</tr>
<tr>
<td>Description</td>
<td>Gets the address at which the BRK exception occurred.</td>
</tr>
<tr>
<td>Arguments</td>
<td>None</td>
</tr>
<tr>
<td>Return Value</td>
<td>Address where BRK exception occurred + 1</td>
</tr>
<tr>
<td>Remarks</td>
<td>This function is declared in #pragma inline_asm. If the R_ROM_MakePatch function is altered to change the capacity of the stack where the data is saved, this function should be modified to match.</td>
</tr>
</tbody>
</table>

### Set_return_adr

<table>
<thead>
<tr>
<th>Outline</th>
<th>Set return address to corresponding patch program</th>
</tr>
</thead>
<tbody>
<tr>
<td>Header</td>
<td>r_rom_correction.h</td>
</tr>
<tr>
<td>Declaration</td>
<td>uint32_t set_return_adr (uint32_t return_adr)</td>
</tr>
<tr>
<td>Description</td>
<td>Sets the address to return to from the BRK exception handler.</td>
</tr>
<tr>
<td>Arguments</td>
<td>uint32_t return_adr: State address of applicable patch program</td>
</tr>
<tr>
<td>Return Value</td>
<td>None</td>
</tr>
<tr>
<td>Remarks</td>
<td>This function is declared in #pragma inline_asm. If the R_ROM_MakePatch function is altered to change the capacity of the stack where the data is saved, this function should be modified to match.</td>
</tr>
</tbody>
</table>

### chk_apply_patch

<table>
<thead>
<tr>
<th>Outline</th>
<th>Patch present/absent determination processing</th>
</tr>
</thead>
<tbody>
<tr>
<td>Header</td>
<td>r_rom_correction.h</td>
</tr>
<tr>
<td>Declaration</td>
<td>static rom_correct_err_t chk_apply_patch (void)</td>
</tr>
<tr>
<td>Description</td>
<td>Checks the patch present/absent determination.</td>
</tr>
<tr>
<td>Arguments</td>
<td>None</td>
</tr>
<tr>
<td>Return Value</td>
<td>Patch present/absent checking result</td>
</tr>
<tr>
<td></td>
<td>ROM_CORRECT_SUCCESS: Patch present</td>
</tr>
<tr>
<td></td>
<td>ROM_CORRECT_NOT_APPLY: No valid data in patch present/absent determination</td>
</tr>
<tr>
<td>Remarks</td>
<td></td>
</tr>
</tbody>
</table>
**setting_patch**

<table>
<thead>
<tr>
<th>Outline</th>
<th>Set patch to register</th>
</tr>
</thead>
<tbody>
<tr>
<td>Header</td>
<td>r_rom_correction.h</td>
</tr>
<tr>
<td>Declaration</td>
<td>static rom_correct_err_t setting_patch (void)</td>
</tr>
<tr>
<td>Description</td>
<td>Registers the patch set in the table data area and patch area, and stores the table data count.</td>
</tr>
<tr>
<td>Arguments</td>
<td>None</td>
</tr>
<tr>
<td>Return Value</td>
<td>Execution result</td>
</tr>
</tbody>
</table>

<table>
<thead>
<tr>
<th>ROM_CORRECT_SUCCESS:</th>
<th>Success</th>
</tr>
</thead>
<tbody>
<tr>
<td>ROM_CORRECT_ERR_BUSY:</td>
<td>Software command running, or flash FIT module not initialized</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_FAILURE:</td>
<td>Flash blank check, erase, or write failure</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_BYTES:</td>
<td>Flash write or blank check size error</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_ADDRESS:</td>
<td>Invalid address setting</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_BLOCKS:</td>
<td>Invalid flash block number</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_TABLE:</td>
<td>Table data area setting error</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_PATCH:</td>
<td>Patch area setting error</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_WR_COPY_FLAG:</td>
<td>Copy area rewrite finished flag write error</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_WR_PATCH_FLAG:</td>
<td>Patch application area rewrite finished flag write error</td>
</tr>
</tbody>
</table>

**chk_patch**

<table>
<thead>
<tr>
<th>Outline</th>
<th>Check patch to register</th>
</tr>
</thead>
<tbody>
<tr>
<td>Header</td>
<td>r_rom_correction.h</td>
</tr>
<tr>
<td>Declaration</td>
<td>static rom_correct_err_t chk_patch (const table_data_t table_data)</td>
</tr>
<tr>
<td>Description</td>
<td>Checks the patch set in the table data area and patch area.</td>
</tr>
<tr>
<td>Arguments</td>
<td>const table_data_t table_data: Target table data</td>
</tr>
<tr>
<td>Return Value</td>
<td>Execution result</td>
</tr>
</tbody>
</table>

<table>
<thead>
<tr>
<th>ROM_CORRECT_SUCCESS:</th>
<th>Success</th>
</tr>
</thead>
<tbody>
<tr>
<td>ROM_CORRECT_ERR_BUSY:</td>
<td>Software command running, or flash FIT module not initialized</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_FAILURE:</td>
<td>Flash blank check, erase, or write failure</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_BYTES:</td>
<td>Flash write or blank check size error</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_ADDRESS:</td>
<td>Invalid address setting</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_BLOCKS:</td>
<td>Invalid flash block number</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_TABLE:</td>
<td>Table data area setting error</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_PATCH:</td>
<td>Patch area setting error</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_WR_COPY_FLAG:</td>
<td>Copy area rewrite finished flag write error</td>
</tr>
<tr>
<td>ROM_CORRECT_ERR_WR_PATCH_FLAG:</td>
<td>Patch application area rewrite finished flag write error</td>
</tr>
</tbody>
</table>

Remarks
chk_table_data
Outline  Check table data
Header    r_rom_correction.h
Declaration  rom_correct_err_t chk_table_data (const table_data_t table_data)
Description  Checks whether the target table data is set correctly.
Arguments  const table_data_t table_data: Target table data
Return Value  Target table data checking result

ROM_CORRECT_SUCCESS:  Target table data correct
ROM_CORRECT_ERR_TABLE:  Target table data not correct
Remarks

chk_patch_area
Outline  Check patch area
Header    r_rom_correction.h
Declaration  rom_correct_err_t chk_patch_area (const uint32_t pp_adr)
Description  Checks whether the target patch area is set correctly.
Arguments  const uint32_t pp_adr: PP_ADR of target table data
Return Value  Target patch area checking result

ROM_CORRECT_SUCCESS:  Target patch area correct
ROM_CORRECT_ERR_PATCH:  Target patch area not correct
Remarks

chk_rewrite_patch_target_area
Outline  Check patch application area rewrite
Header    r_rom_correction.h
Declaration  rom_correct_err_t chk_rewrite_patch_target_area (const table_data_t table_data)
Description  Checks rewriting of the patch application area.
Arguments  const table_data_t table_data: Target table data
Return Value  Execution result

ROM_CORRECT_SUCCESS:  Success
ROM_CORRECT_ERR_BUSY:  Software command running, or flash FIT module not initialized
ROM_CORRECT_ERR_FAILURE:  Flash blank check, erase, or write failure
ROM_CORRECT_ERR_BYTES:  Flash write or blank check size error
ROM_CORRECT_ERR_ADDRESS:  Invalid address setting
ROM_CORRECT_ERR_BLOCKS:  Invalid flash block number
ROM_CORRECT_ERR_WR_COPY_FLAG:  Copy area rewrite finished flag write error
ROM_CORRECT_ERR_WR_PATCH_FLAG:  Patch application area rewrite finished flag write error
Remarks
### rewrite_patch_target_area

**Outline**
Patch application area rewrite processing

**Header**
r_rom_correction.h

**Declaration**
rom_correct_err_t rewrite_patch_target_area (const table_data_t_t table_data)

**Description**
Rewrites the patch application area.

**Arguments**
const table_data_t table_data: Target table data

**Return Value**
Execution result

- ROM_CORRECT_SUCCESS: Success
- ROM_CORRECT_ERR_BUSY: Software command running, or flash FIT module not initialized
- ROM_CORRECT_ERR_FAILURE: Flash blank check, erase, or write failure
- ROM_CORRECT_ERR_BYTES: Flash write or blank check size error
- ROM_CORRECT_ERR_ADDRESS: Invalid address setting
- ROM_CORRECT_ERR_BLOCKS: Invalid flash block number
- ROM_CORRECT_ERR_WR_COPY_FLAG: Copy area rewrite finished flag write error
- ROM_CORRECT_ERR_WR_PATCH_FLAG: Patch application area rewrite finished flag write error

**Remarks**

### chk_rewrite_copy_area

**Outline**
Check copy area rewrite

**Header**
r_rom_correction.h

**Declaration**
rom_correct_err_t chk_rewrite_copy_area (const table_data_t table_data)

**Description**
Checks rewriting of the copy area.

**Arguments**
const table_data_t table_data: Target table data

**Return Value**
Execution result

- ROM_CORRECT_SUCCESS: Success
- ROM_CORRECT_ERR_BUSY: Software command running, or flash FIT module not initialized
- ROM_CORRECT_ERR_FAILURE: Flash blank check, erase, or write failure
- ROM_CORRECT_ERR_BYTES: Flash write or blank check size error
- ROM_CORRECT_ERR_ADDRESS: Invalid address setting
- ROM_CORRECT_ERR_BLOCKS: Invalid flash block number
- ROM_CORRECT_ERR_WR_COPY_FLAG: Copy area rewrite finished flag write error

**Remarks**


**rewrite_copy_area**

**Outline**
Copy area rewrite processing

**Header**
r_rom_correction.h

**Declaration**
static flash_err_t rewrite_copy_area (const uint32_t pp_adr)

**Description**
Rewrites the copy area with data from the patch application area.
The data is saved to the copy area before rewriting with the BRK instruction in case a
momentary voltage drop or the like while writing to the patch application area causes
the write to fail.

**Arguments**
const uint32_t pp_adr: PP_ADR of target table data

**Return Value**
Execution result
- FLASH_SUCCESS: Success
- FLASH_ERR_BUSY: Software command running, or flash FIT module not
  initialized
- FLASH_ERR_FAILURE: Flash erase or write failure
- FLASH_ERR_BYTES: Flash write size error
- FLASH_ERR_ADDRESS: Invalid address setting
- FLASH_ERR_BLOCKS: Invalid flash block number

**Remarks**

**rewrite_brk_code**

**Outline**
Rewrite patch application area with BRK instruction

**Header**
r_rom_correction.h

**Declaration**
static flash_err_t rewrite_brk_code (const uint32_t pp_adr)

**Description**
Rewrites the rewrite address in the patch application area with the BRK instruction.
The data is saved to the copy area before rewriting with the BRK instruction in case a
momentary voltage drop or the like while writing to the patch application area causes
the write to fail.

**Arguments**
const uint32_t pp_adr: PP_ADR of target table data

**Return Value**
FLASH_SUCCESS: Success
- FLASH_ERR_BUSY: Software command running, or flash FIT module not
  initialized
- FLASH_ERR_FAILURE: Flash erase or write failure
- FLASH_ERR_BYTES: Flash write size error
- FLASH_ERR_ADDRESS: Invalid address setting
- FLASH_ERR_BLOCKS: Invalid flash block number

**Remarks**

**call_R_FLASH_Open**

**Outline**
Flash FIT module initialization, including retry in case of error

**Header**
r_rom_correction.h

**Declaration**
static flash_err_t call_R_FLASH_Open (void)

**Description**
Initializes the flash FIT module. Includes retry in case of error.

**Arguments**
None

**Return Value**
FLASH_SUCCESS: Success
- FLASH_ERR_BUSY: Software command running, or flash FIT module not
  initialized

**Remarks**
### call_R_FLASH_Erase

**Outline**
Erase flash, including retry in case of error

**Header**
r_rom_correction.h

**Declaration**
static flash_err_t call_R_FLASH_Erase(uint32_t block_start_address, uint32_t num_blocks)

**Description**
Erased the flash memory. (Includes retry in case of error.)

**Arguments**
- uint32_t block_start_address: Start address of erase target block
- uint32_t num_blocks: Number of target blocks to be erased

**Return Value**
- FLASH_SUCCESS: Success
- FLASH_ERR_BUSY: Software command running, or flash FIT module not initialized
- FLASH_ERR_FAILURE: Flash erase failure
- FLASH_ERR_ADDRESS: Invalid address setting
- FLASH_ERR_BLOCKS: Invalid flash block number

**Remarks**

### call_R_FLASH_BlankCheck

**Outline**
Flash blank check, including retry in case of error

**Header**
r_rom_correction.h

**Declaration**
static flash_err_t call_R_FLASH_BlankCheck(uint32_t address, uint32_t num_bytes, flash_res_t *result)

**Description**
Performs a blank check on the flash memory. (Includes retry in case of error.)

**Arguments**
- uint32_t address: Blank check start address
- uint32_t num_bytes: Blank check byte count
- flash_res_t *result: Pointer to blank check result

**Return Value**
- FLASH_SUCCESS: Success
- FLASH_ERR_BUSY: Software command running, or flash FIT module not initialized
- FLASH_ERR_FAILURE: Blank check of flash memory failure
- FLASH_ERR_BYTES: Flash memory blank check size error
- FLASH_ERR_ADDRESS: Invalid address setting

**Remarks**

### call_R_FLASH_Write

**Outline**
Write to flash, including retry in case of error

**Header**
r_rom_correction.h

**Declaration**
static flash_err_t call_R_FLASH_Write(uint32_t src_address, uint32_t dest_address, uint32_t num_bytes)

**Description**
Writes to the flash memory. (Includes retry in case of error.)

**Arguments**
- uint32_t src_address: Start address where write data is stored
- uint32_t dest_address: Start address of write destination
- uint32_t num_bytes: Write byte count

**Return Value**
- FLASH_SUCCESS: Success
- FLASH_ERR_BUSY: Software command running, or flash FIT module not initialized
- FLASH_ERR_FAILURE: Write to flash memory failure
- FLASH_ERR_BYTES: Flash memory write size error
- FLASH_ERR_ADDRESS: Invalid address setting

**Remarks**
5. Precautions

5.1 Precautions When Using This Application Note

- The user should write data to the table data area and patch area beforehand using self-rewrite in P/E mode, or the like. Note that when using a serial programmer it is not possible to use a boot program to write the data.
- When writing data to the table data area and patch area, do not write FFh to the reserved areas and empty areas.
- The user’s R_ROM_Correct function sends the last setting result registered in the table data as its return value. If setting result information is needed for each table data item, register each table data item and patch area individually.

5.2 Table Data Area and Patch Area Write Procedure Examples

Examples of the procedures for writing to the table data area and patch area implemented by the user are described below. Figure 5.1 shows a table data area write procedure example. Figure 5.2 shows a write procedure example where the write failed due to a momentary voltage drop or the like. Note that the user should make sure to run a blank check before writing data.

1. Only when applying a patch for the first time, write AA55 AA55h to the patch present/absent determination in the table data area. It is not necessary to write AA55 AA55h to the patch present/absent determination when applying a patch the second or subsequent times.

2. Write data to the table data area and to the patch area, in that order.
   2-1. After writing to the table data area, write the table data rewrite finished flag (inverted value of FLG_ADR).
   2-2. After writing to the patch area, write the patch area rewrite finished flag (inverted value of rewrite address).
   2-3. Repeat steps 2-1 and 2-2 to write additional patch data. If the write fails due to a momentary voltage drop or the like, retry the write in the next empty area. Note that the table data consists of 12-byte sets comprising FLG_ADR, PP_ADR, and the table data rewrite finished flag. For FLG_ADR(m), add 0Ch to the FLG_ADR(m − 1) write address.

Note: Since PP_ADR changes when a write to the patch area fails, you will need to redo the procedure from step 2-1. Also, do not perform an erase if a write fails; write the data to the next area.
<table>
<thead>
<tr>
<th>FLG_ADR</th>
<th>PP_ADR</th>
<th>Table data rewrite finished flag</th>
</tr>
</thead>
<tbody>
<tr>
<td>Blank</td>
<td>Blank</td>
<td>Blank</td>
</tr>
<tr>
<td>...</td>
<td>...</td>
<td>...</td>
</tr>
</tbody>
</table>

[1] Blank, so use as write target.

<table>
<thead>
<tr>
<th>FLG_ADR</th>
<th>PP_ADR</th>
<th>Table data rewrite finished flag</th>
</tr>
</thead>
<tbody>
<tr>
<td>FLG_ADRx</td>
<td>Blank</td>
<td>Blank</td>
</tr>
<tr>
<td></td>
<td>...</td>
<td>...</td>
</tr>
</tbody>
</table>

[2] Write FLG_ADRx

<table>
<thead>
<tr>
<th>FLG_ADR</th>
<th>PP_ADR</th>
<th>Table data rewrite finished flag</th>
</tr>
</thead>
<tbody>
<tr>
<td>FLG_ADRx</td>
<td>Blank</td>
<td>Blank</td>
</tr>
<tr>
<td></td>
<td>...</td>
<td>...</td>
</tr>
</tbody>
</table>


Write to PP_ADR.

<table>
<thead>
<tr>
<th>FLG_ADR</th>
<th>PP_ADR</th>
<th>Table data rewrite finished flag</th>
</tr>
</thead>
<tbody>
<tr>
<td>FLG_ADRx</td>
<td>PP_ADRx</td>
<td>Blank</td>
</tr>
<tr>
<td></td>
<td>...</td>
<td>...</td>
</tr>
</tbody>
</table>

[4] Write PP_ADRx

<table>
<thead>
<tr>
<th>FLG_ADR</th>
<th>PP_ADR</th>
<th>Table data rewrite finished flag</th>
</tr>
</thead>
<tbody>
<tr>
<td>FLG_ADRx</td>
<td>PP_ADRx</td>
<td>Blank</td>
</tr>
<tr>
<td></td>
<td>...</td>
<td>...</td>
</tr>
</tbody>
</table>


<table>
<thead>
<tr>
<th>FLG_ADR</th>
<th>PP_ADR</th>
<th>Table data rewrite finished flag</th>
</tr>
</thead>
<tbody>
<tr>
<td>FLG_ADRx</td>
<td>PP_ADRx</td>
<td>Table data x rewrite finished flag</td>
</tr>
<tr>
<td></td>
<td>...</td>
<td>...</td>
</tr>
</tbody>
</table>

### Figure 5.1 Table Data Area Write Procedure Example

Table data rewrite finished flag

<table>
<thead>
<tr>
<th>FLG_ADR</th>
<th>PP_ADR</th>
<th>Table data rewrite finished flag</th>
</tr>
</thead>
<tbody>
<tr>
<td>FLG_ADX</td>
<td>Blank</td>
<td>Blank</td>
</tr>
<tr>
<td>Blank</td>
<td>Blank</td>
<td>...</td>
</tr>
</tbody>
</table>

**Write to PP_ADR.**

### Figure 5.2 Table Data Area Write Procedure Example where Write Failed Due to Momentary Voltage Drop, Etc.

Table data rewrite finished flag

<table>
<thead>
<tr>
<th>FLG_ADR</th>
<th>PP_ADR</th>
<th>Table data rewrite finished flag</th>
</tr>
</thead>
<tbody>
<tr>
<td>FLG_ADX</td>
<td>Not blank (write failure)</td>
<td>Blank</td>
</tr>
<tr>
<td>Blank</td>
<td>Blank</td>
<td>...</td>
</tr>
</tbody>
</table>

**Write failure due to momentary voltage drop, etc.**

**[1]** Blank, so use as write target.

**[2]** Write failure.

Table data rewrite finished flag

<table>
<thead>
<tr>
<th>FLG_ADR</th>
<th>PP_ADR</th>
<th>Table data rewrite finished flag</th>
</tr>
</thead>
<tbody>
<tr>
<td>FLG_ADX</td>
<td>Not blank (write failure)</td>
<td>Blank</td>
</tr>
<tr>
<td>Blank</td>
<td>Blank</td>
<td>...</td>
</tr>
</tbody>
</table>

**[3]** Treat as invalid area.

### Figure 5.3 Table Data Area Write Procedure Example

Table data rewrite finished flag

<table>
<thead>
<tr>
<th>FLG_ADR</th>
<th>PP_ADR</th>
<th>Table data rewrite finished flag</th>
</tr>
</thead>
<tbody>
<tr>
<td>FLG_ADX</td>
<td>Not blank (write failure)</td>
<td>Blank</td>
</tr>
<tr>
<td>Blank</td>
<td>Blank</td>
<td>...</td>
</tr>
</tbody>
</table>

**[4]** Blank, so use as write target.

**[5]** Blank, so use as write target.
5.3 Adapting Specifications to Other Products

When adapting the source code accompanying this application note to other products, it may be necessary to increase the size of the user stack in some cases. Figure 5.3 and Figure 5.4 show examples of using a 32 KB patch application area on the RX65N.

Also, when using the flash FIT module, change the setting of FLASH_CFG_CODE_FLASH_ENABLE to 1, and refer to 2.15, Programming Code Flash from RAM, in RX Family Flash Module Using Firmware Integration Technology (R01AN2184) when adding sections.

![Figure 5.3 Conceptualization of Patch Area when Using 32 KB Patch Application Area on RX65N](image-url)
Figure 5.4 Conceptualization of Patch Area when Using 32 KB Table Data Area on RX65N

Notes:
1. Each patch present/absent determination has three reserved areas with a fixed size of 128 bytes each (total 384 bytes), and the table data is written successively after the reserved areas. The patch present/absent determination has a value of AA55 AA55h.
2. The table data rewrite finished flag is the inverted value of FLG_ADR.
6. Creating Data for Table Data Area and Patch Area

The method of creating data for the table data area and patch area set by the user is described below, using the patch area as an example.

6.1 Patch Area Data Creation Example

Figure 6.1 shows an example of settings for patch area 0.
The patch area PP_ADR0 is set using #pragma section and, after specifying the patch area rewrite finished flag and rewrite address with const declarations, the patch program code follows. For information on the write procedure, refer to 5.2, Table Data Area and Patch Area Write Procedure Examples.

```c
#pragma section PP_ADR0
/* Patch area rewrite finished flag */
const uint32_t g_rewrite_flg0 = XXXXXXXX;
/* Rewrite address */
const uint32_t g_rewriteadr0 = YYYYYYYY;

void patch_prg0(void)
{
    Applicable patch program processing;
    .
    .
    Processing for jump to specified user program;
}

#pragma section /* End of section */
```

**Figure 6.2  Patch Area Code Example**

In the section above the address is set in e² studio. In the menu bar, click **Project → C/C++ Project Settings.**

**Figure 6.3  Example Section Settings (1/2)**
The Properties for RomCorrect window appears, as shown in Figure 6.4. In **C/C++ Build → Settings → Linker → Section Viewer**, add sections CPP_ADR0 and PPP_ADR0, set the corresponding address, and click the **OK** button.

When you build this project after this, an executable file will be generated with the section data allocated to the specified addresses.

![Figure 6.4  Example Section Settings (2/2)](image-url)
6.2 Example of Procedure for Exporting Data from Patch Area

The procedure for exporting data from a specified memory area is described below.

Connect e² studio to the user system, download the program, and then in the menu bar click **Window → Show View → Memory** to display the **Memory** window (see Figure 6.5).

![Figure 6.5 Displaying Memory Window](image)

The **Memory** window appears, as shown in Figure 6.6. In the **Memory** window, click the **Add Memory Monitor** button.

![Figure 6.6 Memory Window](image)

The **Monitor Memory** window appears, as shown in Figure 6.7. Enter the address of the memory area you wish to view, then click the **OK** button.

![Figure 6.7 Monitor Memory Window](image)
The memory area at the specified address is displayed as shown in Figure 6.8.

![Figure 6.8  Memory Area Display](image)

The method of exporting data from the specified memory area is as follows. Click the Export button in the Memory window (see Figure 6.9).

![Figure 6.9  Exporting Data from a Memory Area](image)
The **Export Memory** window appears, as shown in Figure 6.10. For **Format:** select the file format in which to save the data. The memory area to be exported is **Length:** (bytes), beginning at **Start address:** and ending immediately before **End address:**. For **File name:** specify the name of the file to be saved, then click the **OK** button.

![Export Memory Window](image)

**Figure 6.10  Export Memory Window**
7. Sample Code

Sample code can be downloaded from the Renesas Electronics website.

8. Reference Documents

User's Manual: Hardware
   RX113 Group User's Manual: Hardware (R01UH0448)
   (The latest version can be downloaded from the Renesas Electronics website.)

Technical Update/Technical News
   (The latest information can be downloaded from the Renesas Electronics website.)

   RX Family CC-RX Compiler User's Manual (R20UT3248)
   (The latest version can be downloaded from the Renesas Electronics website.)
## Revision History

<table>
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<th>Date</th>
<th>Description</th>
<th>Page</th>
<th>Summary</th>
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<tbody>
<tr>
<td>1.00</td>
<td>Mar. 10, 2020</td>
<td>—</td>
<td>—</td>
<td>First edition issued</td>
</tr>
</tbody>
</table>
General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)
   A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity.
   Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on
   The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state
   Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins
   Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals
   After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin
   Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between $V_{IL}$(Max.) and $V_{IH}$(Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between $V_{IL}$(Max.) and $V_{IH}$(Min.).

7. Prohibition of access to reserved addresses
   Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products
   Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.
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